

Complementary Silicon Power Plastic Transistors

... designed for low voltage, low-power, high-gain audio amplifier applications.

- Collector-Emitter Sustaining Voltage —
 $V_{CE(sus)} = 25 \text{ Vdc (Min) @ } I_C = 10 \text{ mAdc}$
- High DC Current Gain —
 $h_{FE} = 70 \text{ (Min) @ } I_C = 500 \text{ mAdc}$
 $= 45 \text{ (Min) @ } I_C = 2.0 \text{ Adc}$
 $= 10 \text{ (Min) @ } I_C = 5.0 \text{ Adc}$
- Low Collector-Emitter Saturation Voltage —
 $V_{CE(sat)} = 0.3 \text{ Vdc (Max) @ } I_C = 500 \text{ mAdc}$
 $= 0.75 \text{ Vdc (Max) @ } I_C = 2.0 \text{ Adc}$
- High Current-Gain — Bandwidth Product —
 $f_T = 65 \text{ MHz (Min) @ } I_C$
 $= 100 \text{ mAdc}$
- Annular Construction for Low Leakage —
 $I_{CBO} = 100 \text{ nAdc @ Rated } V_{CB}$

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Base Voltage	V_{CB}	40	Vdc
Collector-Emitter Voltage	V_{CEO}	25	Vdc
Emitter-Base Voltage	V_{EB}	8.0	Vdc
Collector Current — Continuous Peak	I_C	5.0 10	Adc
Base Current	I_B	1.0	Adc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	15 0.12	Watts W/ $^\circ\text{C}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5 0.012	Watts W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$

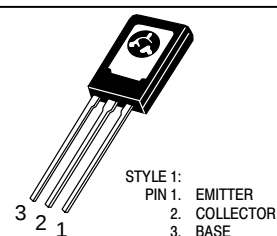
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	θ_{JC}	8.34	$^\circ\text{C/W}$
Thermal Resistance, Junction to Ambient	θ_{JA}	83.4	$^\circ\text{C/W}$

NPN
MJE200*
PNP
MJE210*

*ON Semiconductor Preferred Device

5 AMPERE
POWER TRANSISTORS
COMPLEMENTARY
SILICON
25 VOLTS
15 WATTS



CASE 77-09
TO-225AA

Preferred devices are ON Semiconductor recommended choices for future use and best overall value.

MJE200 MJE210

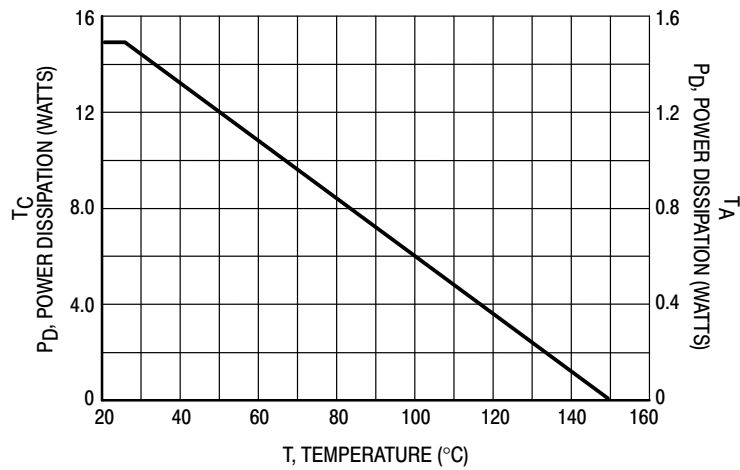


Figure 1. Power Derating

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Sustaining Voltage (1) ($I_C = 10\text{ mAdc}$, $I_B = 0$)	$V_{CEO(sus)}$	25	—	Vdc
Collector Cutoff Current ($V_{CB} = 40\text{ Vdc}$, $I_E = 0$) ($V_{CB} = 40\text{ Vdc}$, $I_E = 0$, $T_J = 125^\circ\text{C}$)	I_{CBO}	— —	100 100	nAdc μAdc
Emitter Cutoff Current ($V_{BE} = 8.0\text{ Vdc}$, $I_C = 0$)	I_{EBO}	—	100	nAdc

ON CHARACTERISTICS

DC Current Gain (1) ($I_C = 500\text{ mAdc}$, $V_{CE} = 1.0\text{ Vdc}$) ($I_C = 2.0\text{ Adc}$, $V_{CE} = 1.0\text{ Vdc}$) ($I_C = 5.0\text{ Adc}$, $V_{CE} = 2.0\text{ Vdc}$)	h_{FE}	70 45 10	— 180 —	—
Collector–Emitter Saturation Voltage (1) ($I_C = 500\text{ mAdc}$, $I_B = 50\text{ mAdc}$) ($I_C = 2.0\text{ Adc}$, $I_B = 200\text{ mAdc}$) ($I_C = 5.0\text{ Adc}$, $I_B = 1.0\text{ Adc}$)	$V_{CE(sat)}$	— — —	0.3 0.75 1.8	Vdc
Base–Emitter Saturation Voltage (1) ($I_C = 5.0\text{ Adc}$, $I_B = 1.0\text{ Adc}$)	$V_{BE(sat)}$	—	2.5	Vdc
Base–Emitter On Voltage (1) ($I_C = 2.0\text{ Adc}$, $V_{CE} = 1.0\text{ Vdc}$)	$V_{BE(on)}$	—	1.6	Vdc

DYNAMIC CHARACTERISTICS

Current–Gain — Bandwidth Product (2) ($I_C = 100\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f_{test} = 10\text{ MHz}$)	f_T	65	—	MHz
Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 0.1\text{ MHz}$)	C_{ob}	— —	80 120	pF

(1) Pulse Test: Pulse Width = 300 μs , Duty Cycle $\approx 2.0\%$.

(2) $f_T = |h_{fe}| \cdot f_{test}$.

MJE200 MJE210

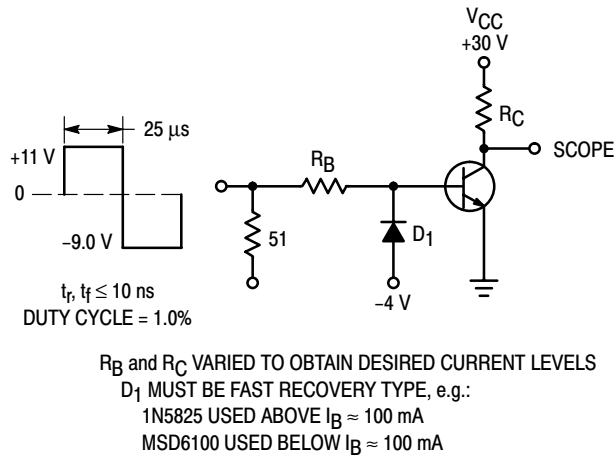


Figure 2. Switching Time Test Circuit

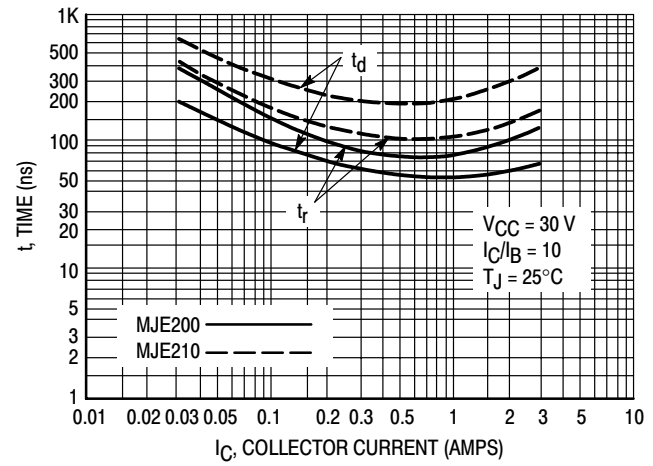


Figure 3. Turn-On Time

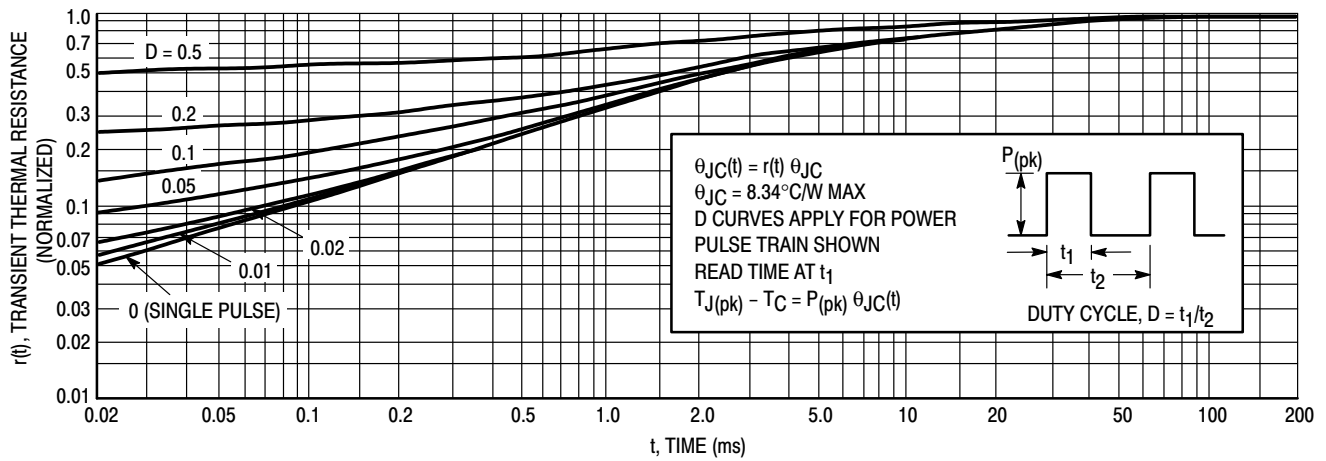


Figure 4. Thermal Response

MJE200 MJE210

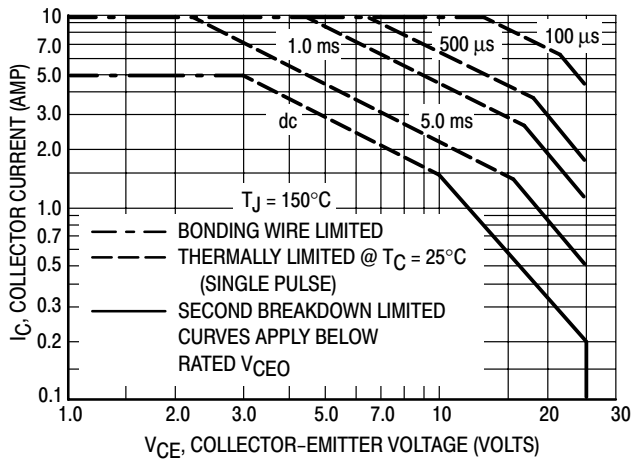


Figure 5. Active Region Safe Operating Area

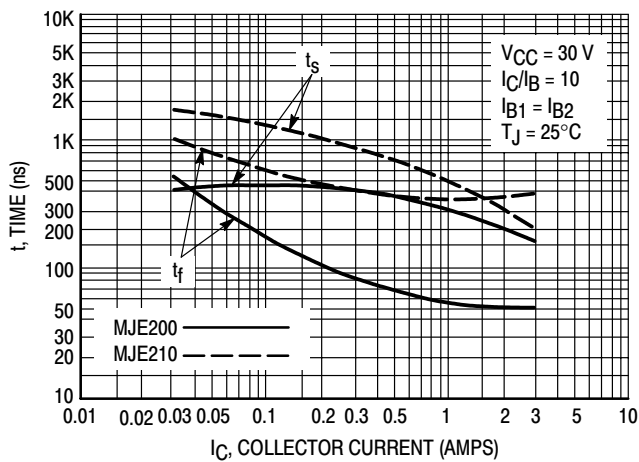


Figure 6. Turn-Off Time

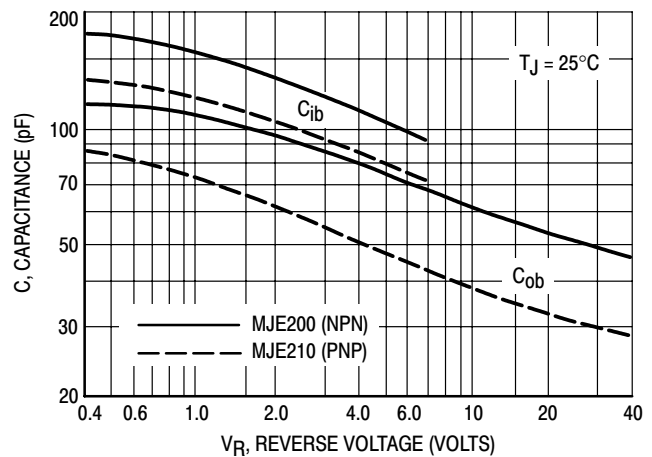


Figure 7. Capacitance

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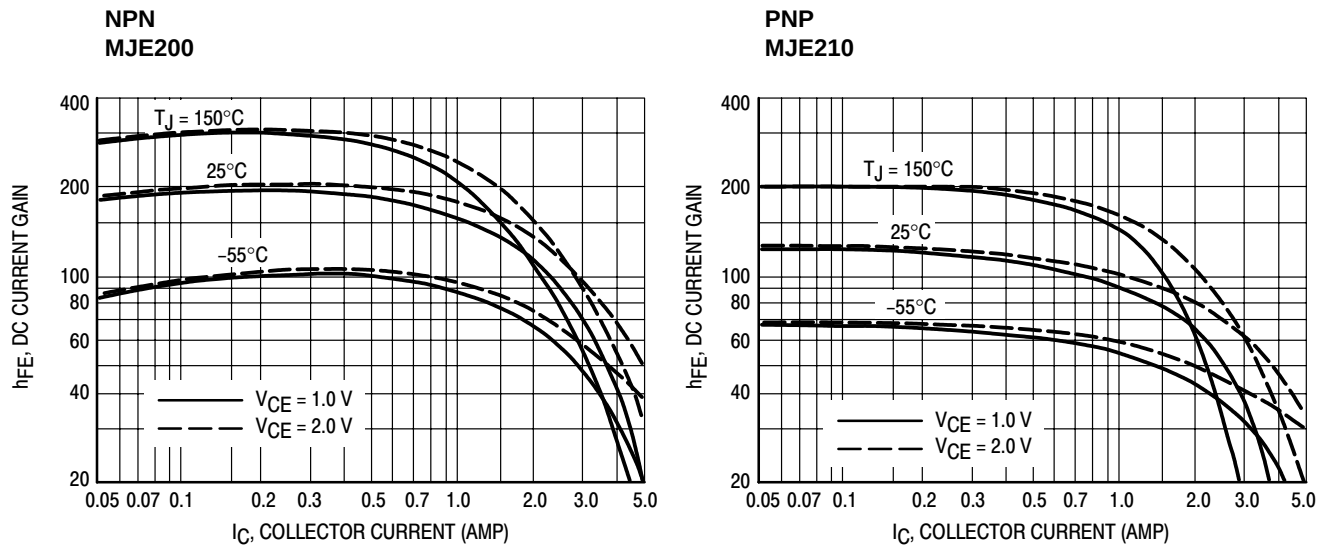


Figure 8. DC Current Gain

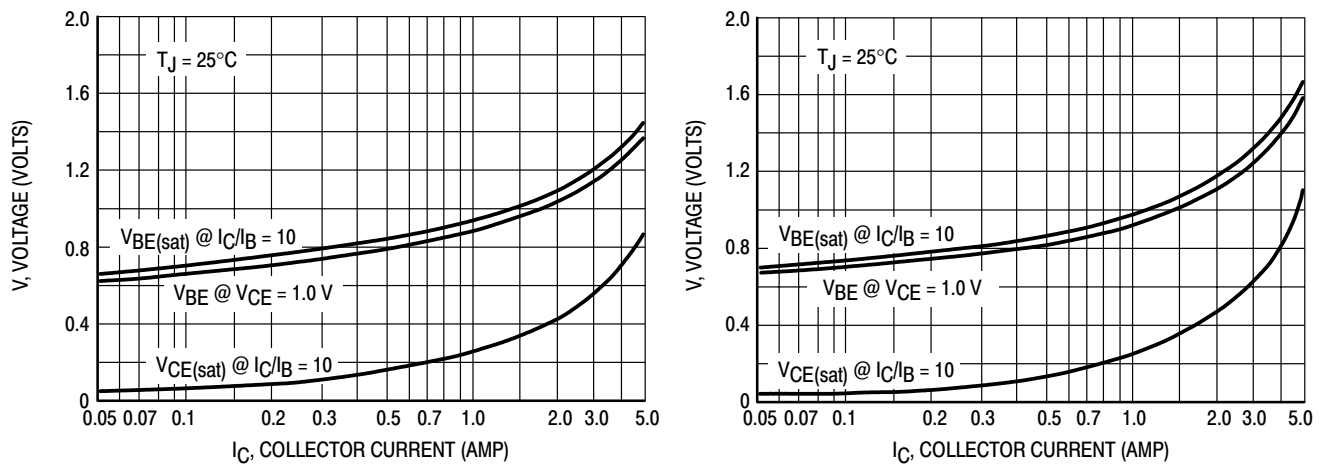


Figure 9. "On" Voltage

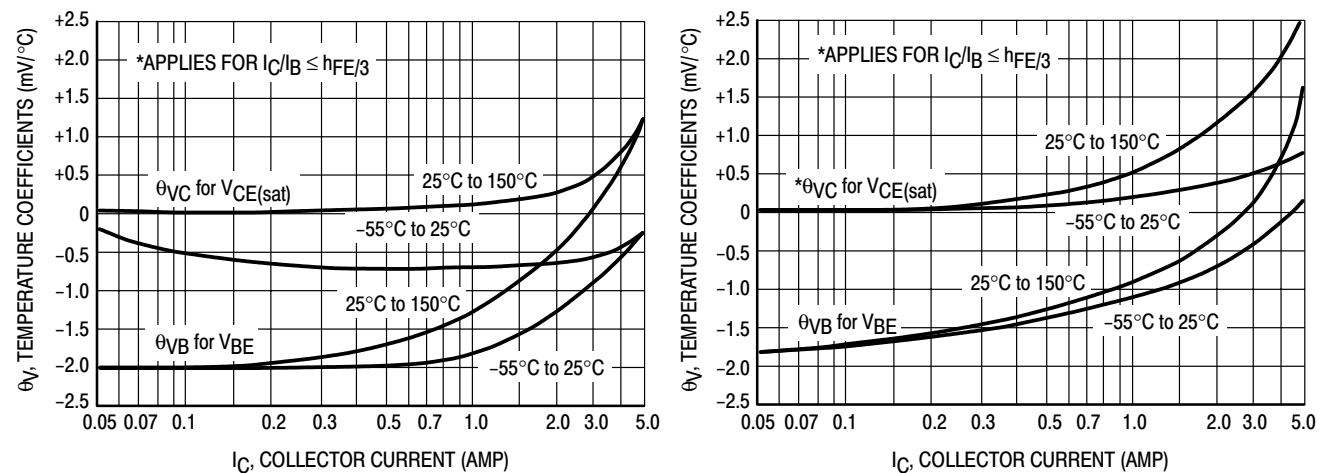
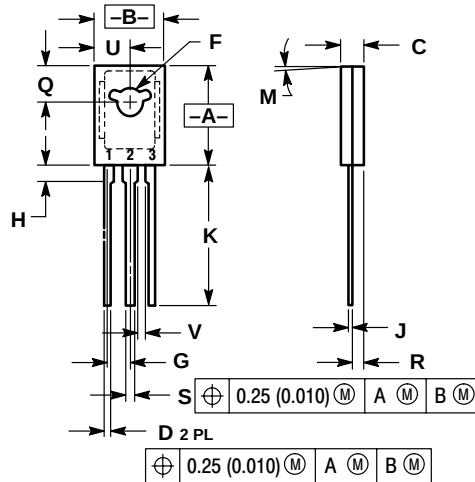


Figure 10. Temperature Coefficients

MJE200 MJE210

PACKAGE DIMENSIONS

TO-225AA
CASE 77-09
ISSUE W



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.425	0.435	10.80	11.04
B	0.295	0.305	7.50	7.74
C	0.095	0.105	2.42	2.66
D	0.020	0.026	0.51	0.66
F	0.115	0.130	2.93	3.30
G	0.094 BSC		2.39 BSC	
H	0.050	0.095	1.27	2.41
J	0.015	0.025	0.39	0.63
K	0.575	0.655	14.61	16.63
M	5° TYP		5° TYP	
Q	0.148	0.158	3.76	4.01
R	0.045	0.065	1.15	1.65
S	0.025	0.035	0.64	0.88
U	0.145	0.155	3.69	3.93
V	0.040	---	1.02	---

STYLE 1:
PIN 1. EMITTER
2. COLLECTOR
3. BASE

Notes

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